**Product data sheet** 

# 1. General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350Z

## 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

# 3. Applications

- DC/DC converters
- · Supply line switching
- Battery charger
- LED backlighting
- Linear voltage regulation (LDO)
- Driver in low supply voltage applications, e.g. lamps, LEDs
- · Inductive load driver (for example relays, buzzers, motors)

# 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-50	V
I <sub>C</sub>	collector current			-	-	-3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	-5	A
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; T <sub>amb</sub> = 25 °C	[1]	-	120	150	mΩ

[1] Pulsed test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ 



50 V, 3 A PNP low VCEsat (BISS) transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В—
3	E	emitter		
4	С	collector	☐1 ☐2 ☐3 SC-73 (SOT223)	Ë sym132

# 6. Ordering information

## **Table 3. Ordering information**

Type number Package					
	Name	Description	Version		
PBSS5350Z	SC-73	plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS5350Z	PB5350

50 V, 3 A PNP low VCEsat (BISS) transistor

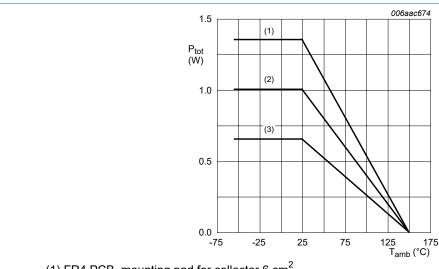
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	А
I <sub>BM</sub>	peak base current			-	-1	А
P <sub>tot</sub>	total power dissipation		[1]	-	0.65	W
			[2]	-	1	W
			[3] [4]	-	1.35	W
			[5]	-	2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), 35 µm single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>. Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [3]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup> Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup> (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

**Power derating curves** Fig. 1.

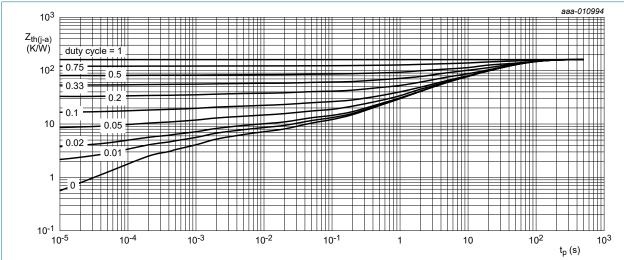
## 50 V, 3 A PNP low VCEsat (BISS) transistor

# 9. Thermal characteristics

**Table 6. Thermal characteristics** 

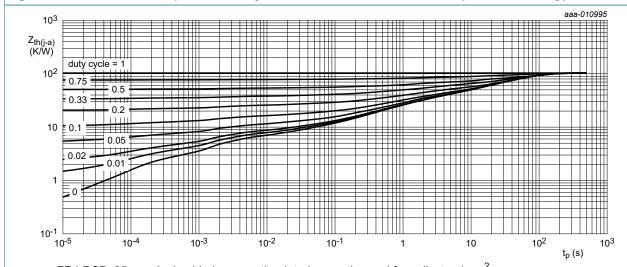
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	-	192	K/W
	junction to ambient	[2]	-	-	125	K/W	
		[3] [4]	-	-	92	K/W	
			[5]	-	-	62.5	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, 35  $\mu m$  single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 35 μm single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3]
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>. [4]
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [5]



FR4 PCB, 35 µm single-sided copper, tin-plated and standard footprint.

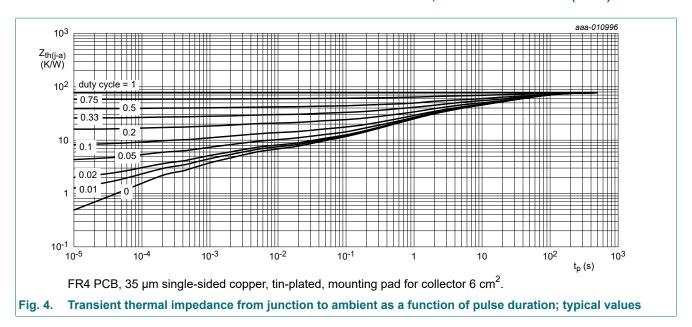
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 50 V, 3 A PNP low VCEsat (BISS) transistor



# 10. Characteristics

#### **Table 7. Characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A		-60	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I <sub>C</sub> = -10 mA; I <sub>B</sub> = 0 A		-50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	I <sub>E</sub> = -100 μA; I <sub>C</sub> = 0 A		-6	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A		-	-	-100	nA
	current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A		-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA		200	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A	[1]	200	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -2 A	[1]	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA		-	-	-100	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA		-	-	-180	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA	[1]	-	-	-300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; T <sub>amb</sub> = 25 °C	[1]	-	120	150	mΩ
$V_{BEsat}$	base-emitter saturation voltage	I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA	[1]	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	[1]	-	-	-1.1	V
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -100 \text{ mA}; f = 100 \text{ MHz}$		100	-	-	MHz

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz	-	-	40	pF

#### [1] Pulsed test: $t_p \le 300 \,\mu s$ ; $\delta \le 0.02$

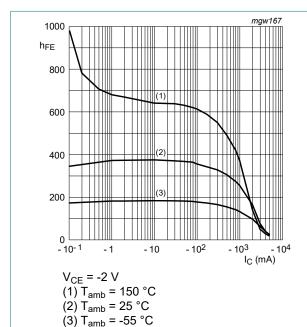


Fig. 5. DC current gain as a function of collector

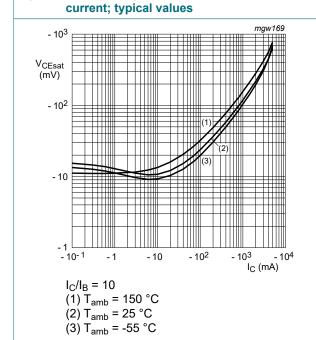


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

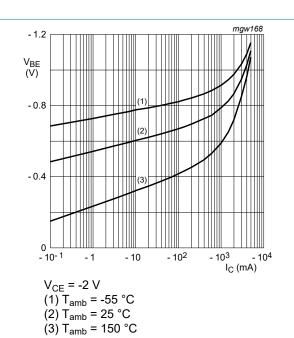


Fig. 6. Base-emitter voltage as a function of collector current; typical values

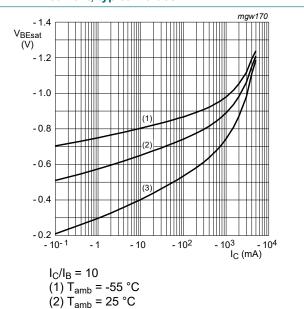
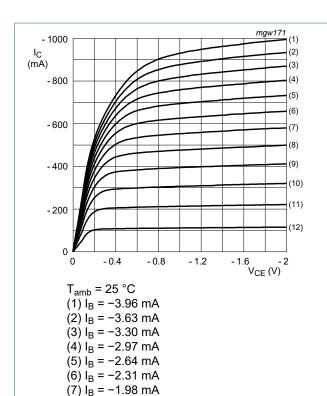


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

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(12) I<sub>B</sub> = −0.33 mA
 Fig. 9. Collector current as a function of collector-emitter voltage; typical values

(8)  $I_B = -1.65 \text{ mA}$ (9)  $I_B = -1.32 \text{ mA}$ 

 $(10) I_B = -0.99 \text{ mA}$ 

 $(11) I_B = -0.66 \text{ mA}$ 

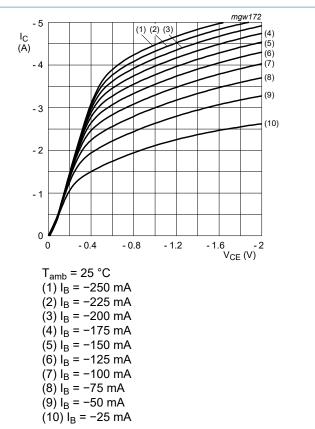
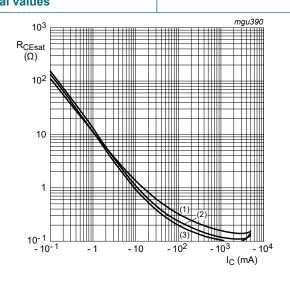


Fig. 10. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$ (1)  $T_{amb} = 150 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

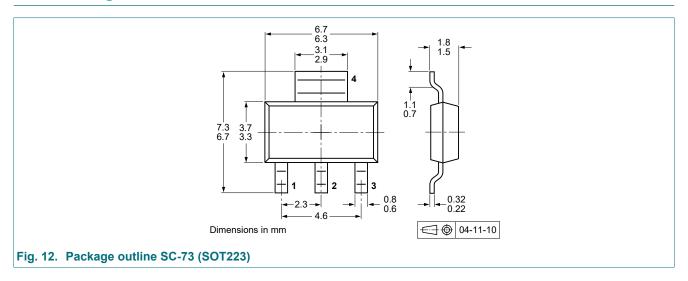
50 V, 3 A PNP low VCEsat (BISS) transistor

# 11. Test information

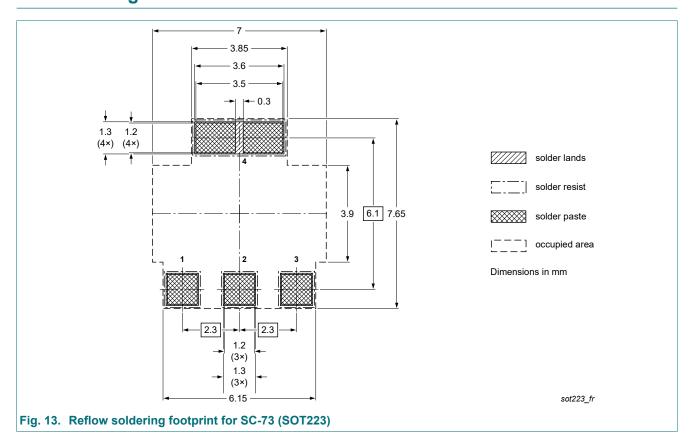
### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

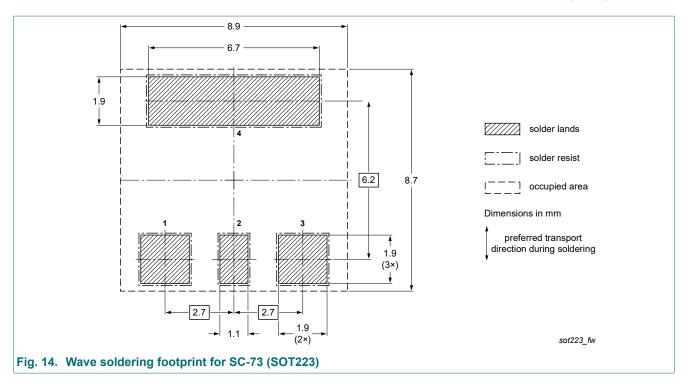
# 12. Package outline



# 13. Soldering



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# 14. Revision history

## **Table 8. Revision history**

-	
Modifications:  • The format of this data sheet has been redesigned to comply with the idea	upersedes
The format of this data sheet has been redesigned to comply with the iden	BSS5350Z v.4
<ul> <li>Legal texts have been adapted to the new company name where appropr</li> </ul>	, -
PBSS5350Z v.4 20030513 Product data sheet - PB	BSS5350Z v.3
PBSS5350Z v.3 20030120 Product data sheet - PB	BSS5350Z v.2
PBSS5350Z v.2 20011113 Product data sheet - PB	BSS5350Z v.1
PBSS5350Z v.1 20010717 Product data sheet	

# 50 V, 3 A PNP low VCEsat (BISS) transistor

# 15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBSS5350Z

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# 50 V, 3 A PNP low VCEsat (BISS) transistor

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